


15V NPN LOW SATURATION TRANSISTOR IN SOT23

Features

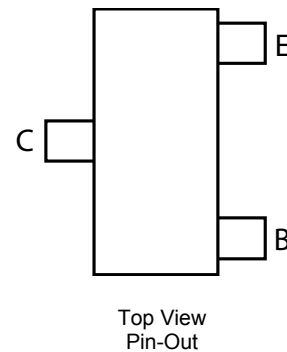
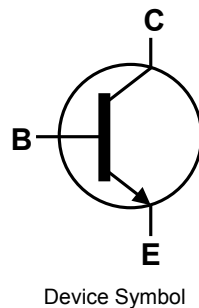
- $BV_{CEO} > 15V$
- $I_C = 3A$ high Continuous Collector Current
- $I_{CM} = 12A$ Peak Pulse Current
- $R_{CE(sat)} = 50m\Omega$ for a low equivalent On-Resistance
- 625mW Power dissipation
- h_{FE} specified up to 12A for high current gain hold up
- Complementary PNP Type: FMMT717
- **Totally Lead-Free & Fully RoHS compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **Qualified to AEC-Q101 Standards for High Reliability**

Mechanical Data

- Case: SOT23
- Case Material: molded plastic, "Green" molding compound
- UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish – Matte Tin Plated Leads, Solderable per MIL-STD-202, Method 208 
- Weight 0.008 grams (approximate)

Applications

- DC-DC / DC-AC Modules
- Regulator
- LED driver
- CCFL Backlighting Inverters

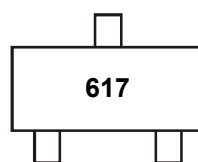


Ordering Information (Note 4)

Product	Marking	Reel size (inches)	Tape width (mm)	Quantity per reel
FMMT617TA	617	7	8	3,000
FMMT617TC	617	13	8	10,000

- Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
 2. See <http://www.diodes.com> for more information about Diodes Incorporated's definitions of Halogen and Antimony free, "Green" and Lead-Free.
 3. Halogen and Antimony free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
 4. For packaging details, go to our website at <http://www.diodes.com>.

Marking Information



617 = Product Type Marking Code

Maximum Ratings (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V_{CBO}	15	V
Collector-Emitter Voltage	V_{CEO}	15	V
Emitter-Base Voltage	V_{EBO}	7	V
Continuous Collector Current	I_C	3	A
Peak Pulse Current (Note 5)	I_{CM}	12	A
Base Current	I_B	500	mA

Thermal Characteristics (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)

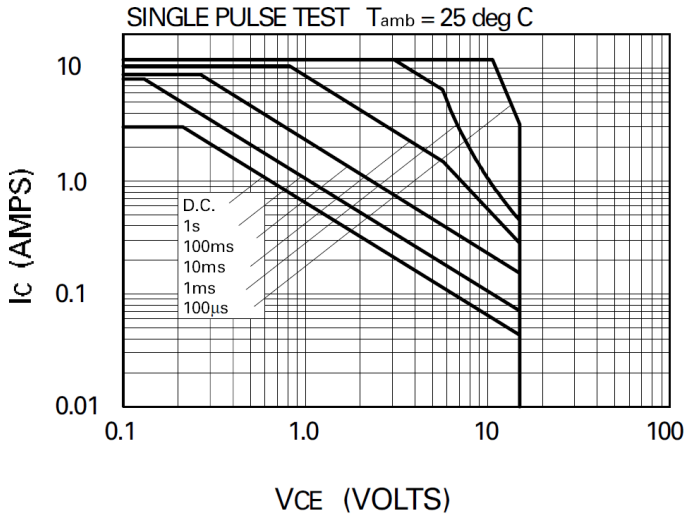
Characteristic	Symbol	Value	Unit
Power Dissipation (Note 5)	P_D	625	mW
Power Dissipation (Note 6)	P_D	806	mW
Thermal Resistance, Junction to Ambient (Note 5)	$R_{\theta JA}$	200	$^\circ\text{C/W}$
Thermal Resistance, Junction to Ambient (Note 6)	$R_{\theta JA}$	155	$^\circ\text{C/W}$
Thermal Resistance, Junction to Leads (Note 7)	$R_{\theta JL}$	194	$^\circ\text{C/W}$
Operating and Storage Temperature Range	T_J, T_{STG}	-55 to +150	$^\circ\text{C}$

ESD Ratings (Note 8)

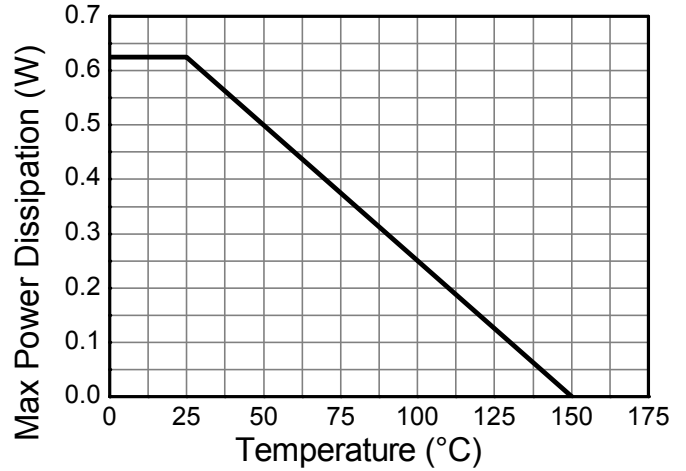
Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	4,000	V	3A
Electrostatic Discharge - Machine Model	ESD MM	≥ 400	V	C

- Notes:
5. For a device surface mounted on 25mm X 25mm FR4 PCB with high coverage of single sided 1 oz copper, in still air conditions; the device is measured when operating in a steady-state condition.
 6. Same as note 5, except the device is measured at $t \leq 5$ sec.
 7. Thermal resistance from junction to solder-point (at the end of the collector lead).
 8. Refer to JEDEC specification JESD22-A114 and JESD22-A115.

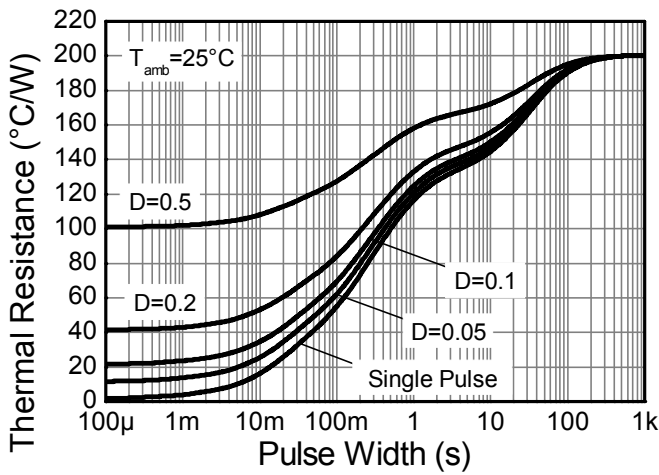
Thermal Characteristics and Derating information



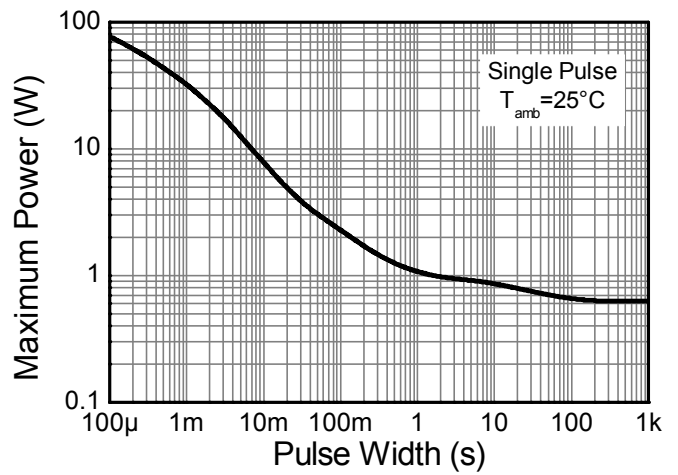
Safe Operating Area



Derating Curve



Transient Thermal Impedance



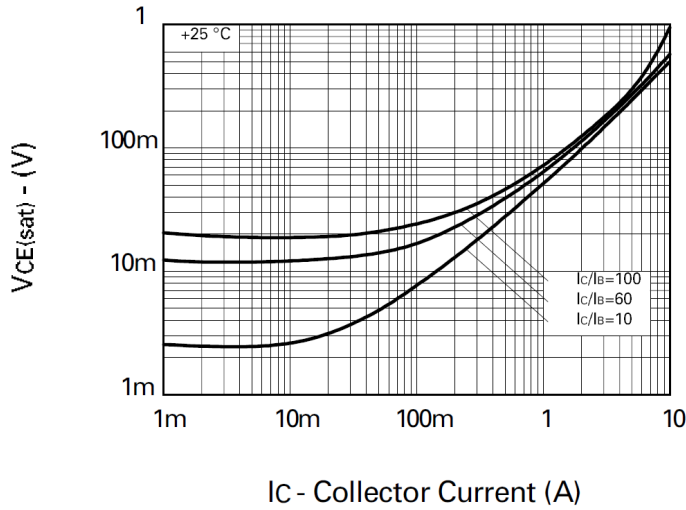
Pulse Power Dissipation

Electrical Characteristics (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)

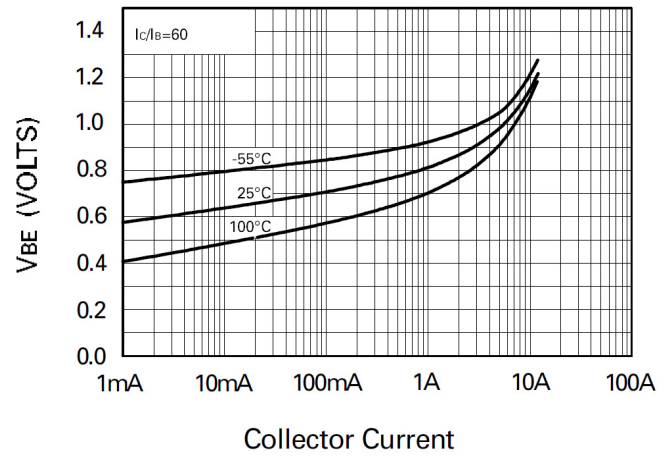
Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
Collector-Base Breakdown Voltage	BV_{CBO}	15	70	-	V	$I_C = 100\mu\text{A}$
Collector-Emitter Breakdown Voltage (Note 9)	BV_{CEO}	15	18	-	V	$I_C = 10\text{mA}$
Emitter-Base Breakdown Voltage	BV_{EBO}	7	8.2	-	V	$I_E = 100\mu\text{A}$
Collector Cut-off Current	I_{CBO}	-	<1	100	nA	$V_{CB} = 10\text{V}$
Emitter Cut-off Current	I_{EBO}	-	<1	100	nA	$V_{EB} = 5.6\text{V}$
Collector Emitter Cut-off Current	I_{CES}	-	<1	100	nA	$V_{CES} = 10\text{V}$
Static Forward Current Transfer Ratio (Note 9)	h_{FE}	200	415	-	-	$I_C = 10\text{mA}, V_{CE} = 2\text{V}$
		300	450	-		$I_C = 200\text{mA}, V_{CE} = 2\text{V}$
		200	320	-		$I_C = 3\text{A}, V_{CE} = 2\text{V}$
		150	240	-		$I_C = 5\text{A}, V_{CE} = 2\text{V}$
		-	80	-		$I_C = 12\text{A}, V_{CE} = 2\text{V}$
Collector-Emitter Saturation Voltage (Note 9)	$V_{CE(sat)}$	-	8	14	mV	$I_C = 0.1\text{A}, I_B = 10\text{mA}$
		-	70	100		$I_C = 1\text{A}, I_B = 10\text{mA}$
		-	150	200		$I_C = 3\text{A}, I_B = 50\text{mA}$
Base-Emitter Saturation Voltage (Note 9)	$V_{BE(sat)}$	-	0.9	1.0	V	$I_C = 3\text{A}, I_B = 50\text{mA}$
Base-Emitter Saturation Voltage (Note 9)	$V_{BE(on)}$	-	0.84	1.0	V	$I_C = 3\text{A}, V_{CE} = 2\text{V}$
Transition Frequency	f_T	80	120	-	MHz	$I_C = 50\text{mA}, V_{CE} = 10\text{V}, f = 50\text{MHz}$
Collector Output Capacitance	C_{obo}	-	30	40	pF	$V_{CB} = 10\text{V}, f = 1\text{MHz}$
Turn-On Time	$t_{(on)}$	-	120	-	ns	$V_{CC} = 10\text{V}, I_C = 3\text{A},$
Turn-Off Time	$t_{(off)}$	-	160	-	ns	$I_{B1} = -I_{B2} = 50\text{mA}$

Notes: 9. Measured under pulsed conditions. Pulse width $\leq 300\mu\text{s}$. Duty cycle $\leq 2\%$

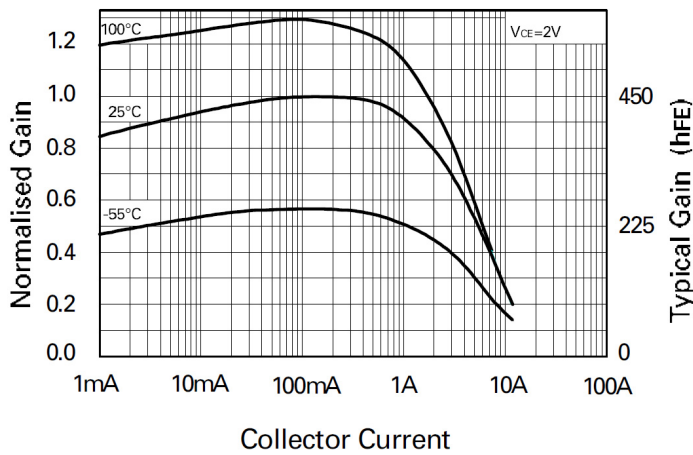
Typical Electrical Characteristics (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)



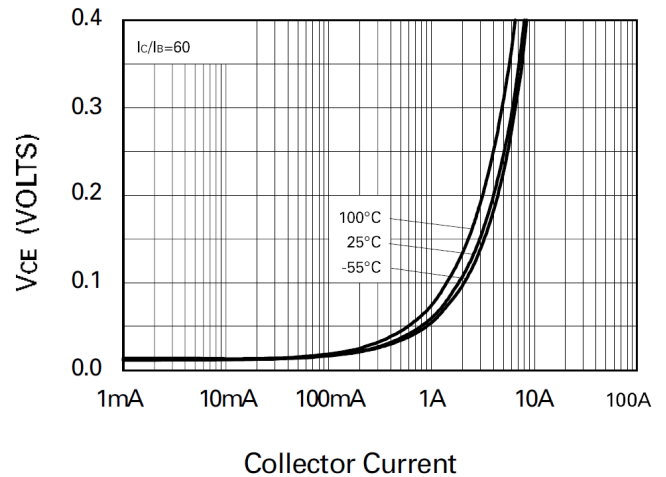
$V_{CE(SAT)}$ v I_C



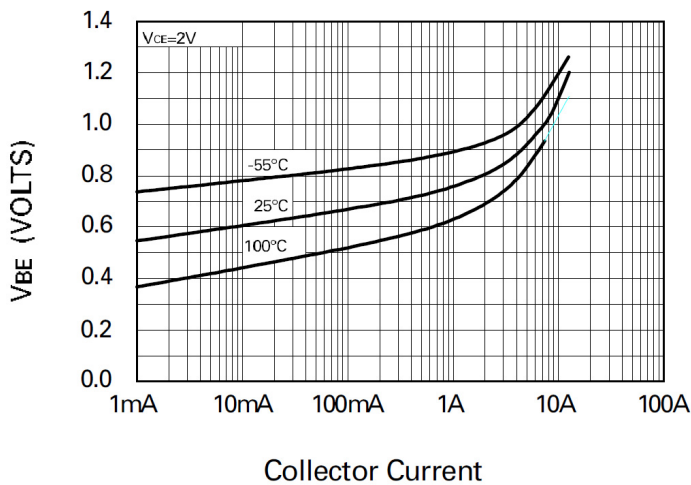
$V_{BE(SAT)}$ vs I_C



hFE vs I_C



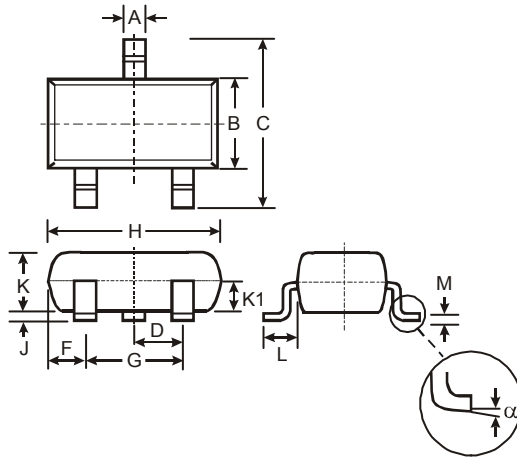
$V_{CE(SAT)}$ vs I_C



$V_{BE(ON)}$ vs I_C

Package Outline Dimensions

Please see AP02002 at <http://www.diodes.com/datasheets/ap02002.pdf> for latest version.

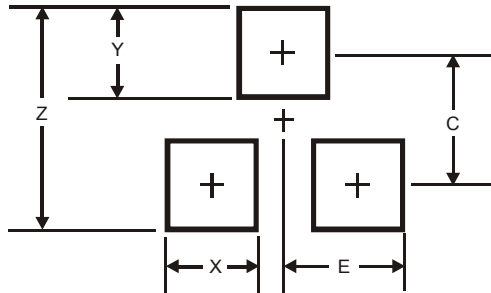


SOT23			
Dim	Min	Max	Typ
A	0.37	0.51	0.40
B	1.20	1.40	1.30
C	2.30	2.50	2.40
D	0.89	1.03	0.915
F	0.45	0.60	0.535
G	1.78	2.05	1.83
H	2.80	3.00	2.90
J	0.013	0.10	0.05
K	0.903	1.10	1.00
K1	-	-	0.400
L	0.45	0.61	0.55
M	0.085	0.18	0.11
α	0°	8°	-

All Dimensions in mm

Suggested Pad Layout

Please see AP02001 at <http://www.diodes.com/datasheets/ap02001.pdf> for the latest version.



Dimensions	Value (in mm)
Z	2.9
X	0.8
Y	0.9
C	2.0
E	1.35

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SuperSOT

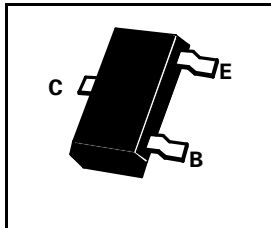
SOT23 NPN SILICON POWER (SWITCHING) TRANSISTORS

ISSUE 3 - NOVEMBER 1995

FMMT617 FMMT618
FMMT619 FMMT624
FMMT625

FEATURES

- * **625mW POWER DISSIPATION**
- * **I_C CONT 3A**
- * 12A Peak Pulse Current
- * Excellent H_{FE} Characteristics Up To 12A (pulsed)
- * Extremely Low Saturation Voltage E.g. 8mV Typ.
- * Extremely Low Equivalent On Resistance; R_{CE(sat)}



DEVICE TYPE	COMPLEMENT	PARTMARKING	R _{CE(sat)}
FMMT617	FMMT717	617	50mΩ at 3A
FMMT618	FMMT718	618	50mΩ at 2A
FMMT619	FMMT720	619	75mΩ at 2A
FMMT624	FMMT723	624	-
FMMT625	-	625	-

ABSOLUTE MAXIMUM RATINGS.

PARAMETER	SYMBOL	FMMT 617	FMMT 618	FMMT 619	FMMT 624	FMMT 625	UNIT
Collector-Base Voltage	V _{CBO}	15	20	50	125	150	V
Collector-Emitter Voltage	V _{CEO}	15	20	50	125	150	V
Emitter-Base Voltage	V _{EBO}	5	5	5	5	5	V
Peak Pulse Current**	I _{CM}	12	6	6	3	3	A
Continuous Collector Current	I_C	3	2.5	2	1	1	A
Base Current	I _B	500					mA
Power Dissipation at T_{amb}=25°C*	P_{tot}	625					mW
Operating and Storage Temperature Range	T _j ; T _{stg}	-55 to +150					°C

* Maximum power dissipation is calculated assuming that the device is mounted on a ceramic substrate measuring 15x15x0.6mm

**Measured under pulsed conditions. Pulse width=300μs. Duty cycle ≤ 2%
Spice parameter data is available upon request for these devices

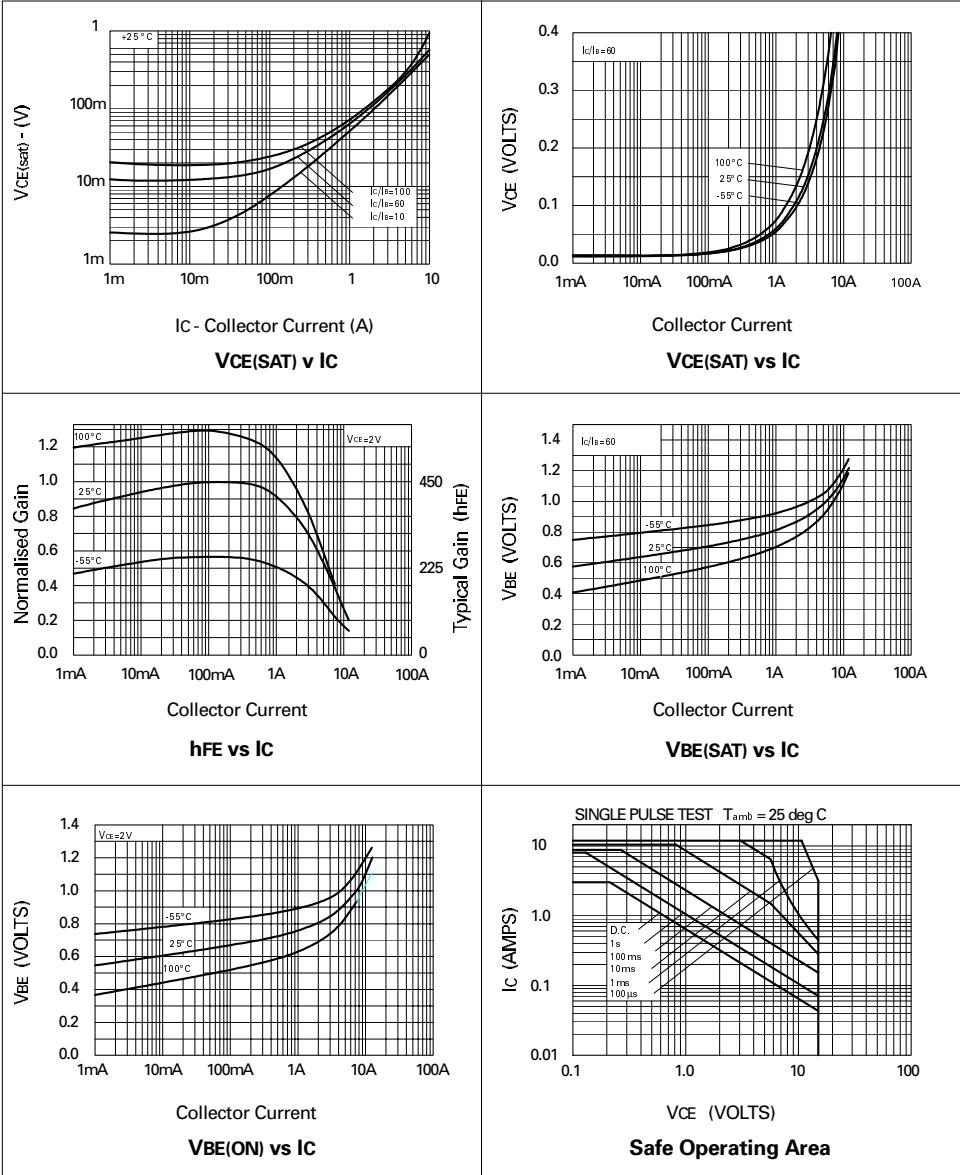
FMMT617

ELECTRICAL CHARACTERISTICS (at $T_{amb} = 25^{\circ}\text{C}$ unless otherwise stated).

PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	CONDITIONS.
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	15	70		V	$I_C=100\mu\text{A}$
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	15	18		V	$I_C=10\text{mA}^*$
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	5	8.2		V	$I_E=100\mu\text{A}$
Collector Cut-Off Current	I_{CBO}			100	nA	$V_{CB}=10\text{V}$
Emitter Cut-Off Current	I_{EBO}			100	nA	$V_{EB}=4\text{V}$
Collector Emitter Cut-Off Current	I_{CES}			100	nA	$V_{CES}=10\text{V}$
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$		8 70 150	14 100 200	mV mV mV	$I_C=0.1\text{A}, I_B=10\text{mA}^*$ $I_C=1\text{A}, I_B=10\text{mA}^*$ $I_C=3\text{A}, I_B=50\text{mA}^*$
Base-Emitter Saturation Voltage	$V_{BE(sat)}$		0.9	1.0	V	$I_C=3\text{A}, I_B=50\text{mA}^*$
Base-Emitter Turn-On Voltage	$V_{BE(on)}$		0.84	1.0	V	$I_C=3\text{A}, V_{CE}=2\text{V}^*$
Static Forward Current Transfer Ratio	h_{FE}	200 300 200 150	415 450 320 240 80			$I_C=10\text{mA}, V_{CE}=2\text{V}^*$ $I_C=200\text{mA}, V_{CE}=2\text{V}^*$ $I_C=3\text{A}, V_{CE}=2\text{V}^*$ $I_C=5\text{A}, V_{CE}=2\text{V}^*$ $I_C=12\text{A}, V_{CE}=2\text{V}^*$
Transition Frequency	f_T	80	120		MHz	$I_C=50\text{mA}, V_{CE}=10\text{V}$ $f=50\text{MHz}$
Output Capacitance	C_{obo}		30	40	pF	$V_{CB}=10\text{V}, f=1\text{MHz}$
Turn-On Time	$t_{(on)}$		120		ns	$V_{CC}=10\text{V}, I_C=3\text{A}$ $I_{B1}=I_{B2}=50\text{mA}$
Turn-Off Time	$t_{(off)}$		160		ns	

*Measured under pulsed conditions. Pulse width=300 μs . Duty cycle $\leq 2\%$

TYPICAL CHARACTERISTICS

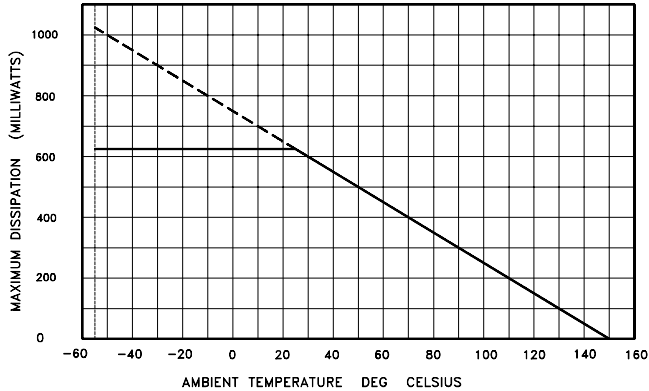


FMMT617 FMMT624
 FMMT618 FMMT625
 FMMT619

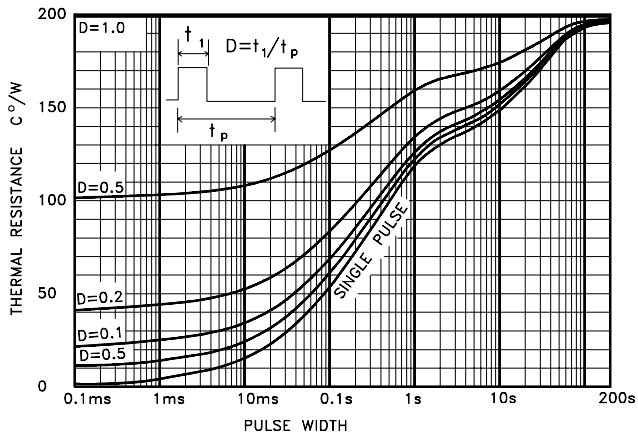
SuperSOT Series

FMMT717 FMMT722
 FMMT718 FMMT723
 FMMT720

THERMAL CHARACTERISTICS AND DERATING INFORMATION



DERATING CURVE



MAXIMUM TRANSIENT THERMAL RESISTANCE

* Reference above figures, Devices were mounted on a 15mmx15mm ceramic substrate